

CD54HC299, CD74HC299, CD54HCT299

Data sheet acquired from Harris Semiconductor SCHS178C

January 1998 - Revised May 2003

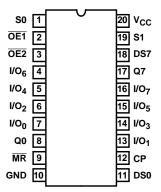
High-Speed CMOS Logic 8-Bit Universal Shift Register; Three-State

Features

- Buffered Inputs
- Four Operating Modes: Shift Left, Shift Right, Load and Store
- Can be Cascaded for N-Bit Word Lengths
- I/O₀ I/O₇ Bus Drive Capability and Three-State for Bus Oriented Applications
- Typical $f_{MAX} = 50MHz$ at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^{o}C$
- Fanout (Over Temperature Range)
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility,
 V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
 - CMOS Input Compatibility, $I_I \le 1\mu A$ at V_{OL} , V_{OH}

Pinout

CD54HC299, CD54HCT299 (CERDIP) CD74HC299, CD74HCT299 (PDIP, SOIC) TOP VIEW



Description

The 'HC259 and 'HCT299 are 8-bit shift/storage registers with three-state bus interface capability. The register has four synchronous-operating modes controlled by the two select inputs as shown in the mode select (S0, S1) table. The mode select, the serial data (DS0, DS7) and the parallel data (I/O $_0$ - I/O $_7$) respond only to the low-to-high transition of the clock (CP) pulse. S0, S1 and data inputs must be stable one setup time prior to the clock positive transition.

The Master Reset (\overline{MR}) is an asynchronous active low input. When \overline{MR} output is low, the register is cleared regardless of the status of all other inputs. The register can be expanded by cascading same units by tying the serial output (Q0) to the serial data (DS7) input of the preceding register, and tying the serial output (Q7) to the serial data (DS0) input of the following register. Recirculating the (n x 8) bits is accomplished by tying the Q7 of the last stage to the DS0 of the first stage.

The three-state input/output I(/O) port has three modes of operation:

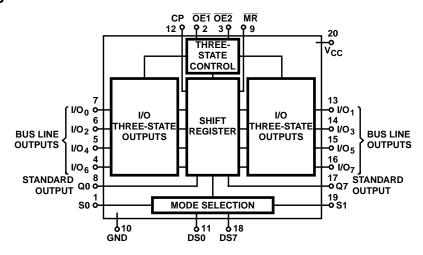
- Both output enable (OE1 and OE2) inputs are low and S0 or S1 or both are low, the data in the register is presented at the eight outputs.
- 2. When both S0 and S1 are high, I/O terminals are in the high impedance state but being input ports, ready for parallel data to be loaded into eight registers with one clock transition regardless of the status of OE1 and OE2.
- Either one of the two output enable inputs being high will force I/O terminals to be in the off-state. It is noted that each I/O terminal is a three-state output and a CMOS buffer input.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC299F3A	-55 to 125	20 Ld CERDIP
CD54HCT299F3A	-55 to 125	20 Ld CERDIP
CD74HC299E	-55 to 125	20 Ld PDIP
CD74HC299M	-55 to 125	20 Ld SOIC
CD74HC299M96	-55 to 125	20 Ld SOIC
CD74HCT299E	-55 to 125	20 Ld PDIP
CD74HCT299M	-55 to 125	20 Ld SOIC
CD74HCT299M96	-55 to 125	20 Ld SOIC

NOTE: When ordering, use the entire part number. The suffix 96 denotes tape and reel.

Functional Diagram



MODE SELECT FUNCTION TABLE THREE-STATE I/O PORT OPERATING MODE

			INPUTS			INPUTS/OUTPUTS
FUNCTION	OE1	OE2	S0	S1	Qn (REGISTER)	I/O0 I/O7
Read Register	L	L	L	Х	L	L
	L	L	L	Х	Н	Н
	L	L	Х	L	L	L
	L	L	Х	L	Н	Н
Load Register	Х	Х	Н	Н	Qn = I/On	I/On = Inputs
Disable I/O	Н	Х	Х	Х	Х	(Z)
	Х	Н	Х	Х	Х	(Z)

TRUTH TABLE

				INPUTS					REGIS	TER OU	TPUTS	
FUNCTION	MR	СР	S0	S0 S1	DS0	DS7	7 I/On	Q0	Q1		Q6	Q7
RESET (CLEAR)	L	Х	Х	х	Х	Х	Х	L	L		L	L
Shift Right	Н	1	h	I	I	Х	Х	L	q ₀		q ₅	q ₆
	Н	1	h	I	h	Х	Х	Н	90		q 5	Q6
Shift Left	Н	1	I	h	Х	I	Х	91	q2		97	L
	Н	1	I	h	Х	h	Х	91	q ₂		97	Н
Hold (Do Nothing)	Н	1	I	I	Х	Х	Х	q ₀	9 1		q ₆	97
Parallel Load	Н	1	h	h	Х	Х	Ī	L	L		L	L
	Н	1	h	h	Х	Х	h	Н	Н		Н	Н

H = Input Voltage High Level, h = Input voltage high one set-up timer prior clock transition; L = Input Voltage Low Level; I = Input voltage low one set-up time prior to clock transition; qn = Lower case letter indicates the state of the reference output one set-up time prior to clock transition; X - Voltage level on logic status don't care; Z = Output in high impedance state, ↑ = Low to High Clock Transition.

Absolute Maximum Ratings DC Supply Voltage, V $_{CC}$-0.5V to 7V DC Input Diode Current, I_{IK} For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ ± 20 mA DC Output Diode Current, I_{OK} DC Drain Current, per Output, I_{O} , For -0.5V < V_{O} < V_{CC} + 0.5V For I/O Outputs.....±35mA DC Output Source or Sink Current per Output Pin, $I_{\mbox{\scriptsize O}}$ **Operating Conditions**

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)
E (PDIP) Package	69
M (SOIC) Package	58
Maximum Junction Temperature	150 ⁰ C
Maximum Storage Temperature Range	65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300 ^o C
(SOIC - Lead Tips Only)	

Temperature Range, T _A	55°C to 125°C
HC Types	2V to 6V
HCT Types	
DC Input or Output Voltage, V _I , V _O	0V to V _{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

1. The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

			EST DITION	s	v _{cc}		25°C		-40°C 1	O 85°C	-55°C T	O 125 ⁰ C	
PARAMETER	SYMBOL	V _I (V)	l _o (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES													
High Level Input	V _{IH}	-		-	2	1.5	-	-	1.5	-	1.5	-	V
Voltage					4.5	3.15	-	-	3.15	-	3.15	-	V
					6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input	V _{IL}	-		-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage					4.5	-	-	1.35	-	1.35	-	1.35	V
					6	-	-	1.8	-	1.8	-	1.8	V
High Level Output	V _{OH}	V _{IH} or V _{IL}	-0	.02	2	1.9	-	-	1.9	-	1.9	-	V
Voltage CMOS Loads					4.5	4.4	-	-	4.4	-	4.4	-	V
OWOC Loads					6	5.9	-	-	5.9	-	5.9	-	V
High Level Output			Qn	I/On	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			-4	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
112 2000			-5.2	-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V _{OL}	V _{IH} or V _{IL}	0.	02	2	-	-	0.1	-	0.1	-	0.1	V
Voltage CMOS Loads					4.5	-	-	0.1	-	0.1	-	0.1	V
ower Loads					6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output			Qn	I/On	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			4 6		4.5	-	-	0.26	-	0.33	-	0.4	V
1122000			5.2	7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	Ι _Ι	V _{CC} or GND		-	6	-	-	±0.1	-	±1	-	±1	μА

DC Electrical Specifications (Continued)

		1	EST DITIONS	V _{CC}		25°C		-40°C T	TO 85°C	-55°C T	O 125°C	4
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Quiescent Device Current	Icc	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μΑ
Three- State Leak- age Current	V _{IL} or V _{IH}	V _O =V _{CC} or GND	-	6	-	-	±0.5	-	±5	-	±10	μА
HCT TYPES	•					•		•				
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{ОН}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	l _l	V _{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	μА
Quiescent Device Current	Icc	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μА
Three- State Leak- age Current	V _{IL} or V _{IH}	V _O =V _{CC} or GND	-	6	-	-	±0.5	-	±5	-	±10	μА
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC} (Note 2)	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μΑ

NOTE:

HCT Input Loading Table

INPUT	UNIT LOADS
S1, MR	0.25
I/O ₀ - I/O ₇	0.25
DS0, DS7	0.25
S0, CP	0.6
OE1, OE2	0.3

NOTE: Unit Load is $\Delta I_{\hbox{CC}}$ limit specific in Static Specifications Table, e.g., 360 μA max. at $25^{o}C.$

^{2.} For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

Prerequisite for Switching Specifications

				25°C		-40	°C TO 8	5°C	-55°C TO 125°C			
PARAMETER	SYMBOL	V _{CC} (V)	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
HC TYPES		!									<u> </u>	
Maximum Clock	f _{MAX}	2	6	-	-	5	-	-	4	-	-	MHz
Frequency		4.5	30	-	-	25	-	-	20	-	-	MHz
		6	35	-	-	29	-	-	23	-	-	MHz
MR Pulse Width	t _W	2	50	-	-	65	-	-	75	-	-	ns
		4.5	10	-	-	13	-	-	15	-	-	ns
		6	9	-	-	11	-	-	13	-	-	ns
Clock Pulse Width	t _W	2	80	-	-	100	-	-	120	-	-	ns
		4.5	16	-	-	20	-	-	24	-	-	ns
		6	14	-	-	17	-	-	20	-	-	ns
Setup Time	t _{SU}	2	100	-	-	125	-	-	150	-	-	ns
DS0, DS7, I/On to Clock		4.5	20	-	-	25	-	-	30	-	-	ns
		6	17	-	-	21	-	-	26	-	-	ns
Hold Time DS0, DS7, I/On, S0, S1 to Clock	t _H	2	0	-	-	0	-	-	0	-	-	ns
		4.5	0	-	-	0	-	-	0	-	-	ns
		6	0	-	-	0	-	-	0	-	-	ns
Recovery Time	t _{REC}	2	5	-	-	5	-	-	5	-	-	ns
MR to Clock		4.5	5	-	-	5	-	-	5	-	-	ns
		6	5	-	-	5	-	-	5	-	-	ns
Setup Time	t _{SU}	2	120	-	-	150	-	-	180	-	-	ns
S1, S0 to Clock		4.5	24	-	-	30	-	-	36	-	-	ns
		6	20	-	-	26	-	-	31	-	-	ns
HCT TYPES												
Maximum Clock Frequency	f _{MAX}	4.5	25	-	-	20	-	-	16	-	-	MHz
MR Pulse Width	t _W	4.5	15	-	-	19	-	-	22	-	-	ns
Clock Pulse Width	t _W	4.5	20	-	-	25	-	-	30	-	-	ns
Setup Time DS0, DS7, I/On, S0, S1 to Clock	t _{SU}	4.5	20	-	-	25	-	-	30	-	-	ns
Hold Time DS0, DS7, I/On, S0, S1 to Clock	t _H	4.5	0	-	-	0	-	-	0	-	-	ns
Recovery Time MR to Clock	tREC	4.5	5	-	-	5	-	-	5	-	-	ns
Setup Time S1, S0 to Clock	t _{SU}	4.5	27	-	-	34	-	-	41	-	-	ns

Switching Specifications $C_L = 50pF$, Input t_f , $t_f = 6ns$

		TEST			25°C			C TO °C	-55°C TO 125°C		-	
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS	
HC TYPES										-		
Propagation Delay	t _{PLH} , t _{PHL}	$C_L = 50pF$										
Clock to I/O Output, Clock to Q0 and Q7,			2	-	-	200	-	250	-	300	ns	
MR to Output			4.5	-	-	40	-	50	-	60	ns	
		C _L = 15pF	5	-	17	-	-	-	-	-	ns	
		C _L = 50pF	6	-	-	34	-	43	-	51	ns	
Output Enable and Disable Times	^t PZL	C _L = 15pF	5	-	10	-	-	-	-	-	ns	
Times	t _{PZH} , t _{PLZ}			ı	13	-	1	-	-	-	ns	
	t _{PHZ}			-	15	-	-	-	-	-	ns	
Output High-Z to High Level	t _{PZH}	C _L = 50pF	2	-	-	155	-	195	-	235	ns	
			4.5	-	-	31	-	39	-	47	ns	
			6	-	-	26	-	33	-	40	ns	
Output High Level to High-Z	t _{PHZ}	C _L = 50pF	2	-	-	185	-	230	-	280	ns	
			4.5	-	-	37	-	46	-	56	ns	
			6	-	-	31	-	39	-	48	ns	
Output Low Level to High-Z	t _{PLZ}	C _L = 50pF	2	-	-	155	-	195	-	235	ns	
				4.5	-	-	31	-	39	-	47	ns
			6	-	-	26	-	33	-	40	ns	
Output High-Z to Low Level	t _{PZL}	C _L = 50pF	2	-	-	130	-	165	-	195	ns	
			4.5	-	-	26	-	33	-	39	ns	
			6	-	-	22	-	28	-	33	ns	
Output Transition Time	t _{THL} , t _{TLH}	C _L = 50pF										
Q0, Q7			2	-	-	75	-	95	-	110	ns	
			4.5	-	-	15	-	19	-	22	ns	
			6	-	-	13	-	16	-	19	ns	
I/O ₀ to I/O ₇	t _{THL} , t _{TLH}	C _L = 50pF	2	-	-	60	-	75	-	90	ns	
			4.5	-	-	12	-	15	-	18	ns	
			6	-	-	10	-	13	-	15	ns	
Input Capacitance	C _I	C _L = 50pF	-	10	-	10	-	10	-	10	pF	
Three-State Output Capacitance	CO	-	-	20	-	20	-	20	-	20	pF	
Power Dissipation Capacitance (Notes 3, 4)	C _{PD}	C _L = 15pF	5	-	150	-	-	-	-	-	pF	

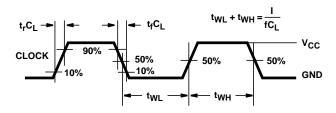
Switching Specifications $C_L = 50pF$, Input t_r , $t_f = 6ns$ (Continued)

		TEST			25°C			С ТО °С		C TO 5°C	
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HCT TYPES											
Propagation Delay	t _{PHL} , t _{PLH}										
Clock to I/O Output, Clock to Q0 and Q7		$C_L = 50pF$	4.5	-	-	45	-	56	-	68	ns
Clock to Qu and Q1		C _L = 15pF	5	-	19	-	-	-	-	-	ns
MR to Output	t _{PHL} , t _{PLH}	C _L = 50pF	4.5	-	-	46	-	58	-	69	ns
Output Enable and Disable Times	t _{PZL} , t _{PZH} , t _{PLZ} , t _{PHZ}	C _L = 15pF	5	-	10, 13, 15	-	-	-	-	-	ns
Output High-Z to High Level	t _{PZH}	C _L = 50pF	4.5	-	-	32	-	40	-	48	ns
Output High Level to High-Z	t _{PHZ}	C _L = 50pF	4.5	-	-	37	-	46	-	56	ns
Output Low Level to High-Z	t _{PLZ}	C _L = 50pF	4.5	-	-	32	-	40	-	48	ns
Output High-Z to Low Level	t _{PZL}	C _L = 50pF	4.5	-	-	30	-	38	-	45	ns
Output Transition Time Q0, Q7	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	-	15	-	19	-	22	ns
I/O ₀ to I/O ₇		C _L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C _{IN}	C _L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	CO	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C _{PD}	C _L = 15pF	5	ī	170	í	-	-	-	-	pF

NOTES:

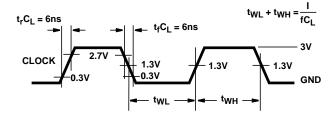
- 3. $C_{\mbox{\scriptsize PD}}$ is used to determine the dynamic power consumption, per register.
- 4. $P_D = C_{PD} \, V_{CC}^2 \, f_i + \sum (C_L \, V_{CC}^2 \, f_O)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V $_{CC}$ to 90% V $_{CC}$ in accordance with device truth table. For f_{MAX} , input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX} , input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

Test Circuits and Waveforms (Continued)

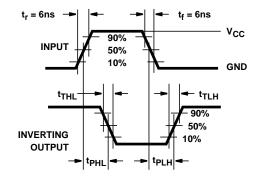


FIGURE 3. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

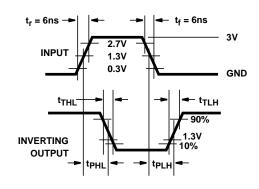


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

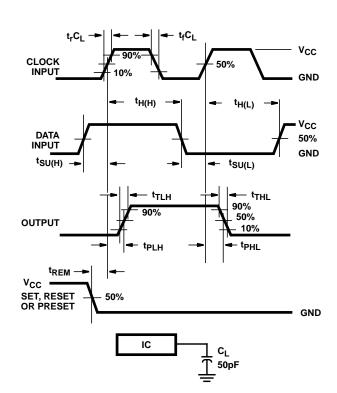


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

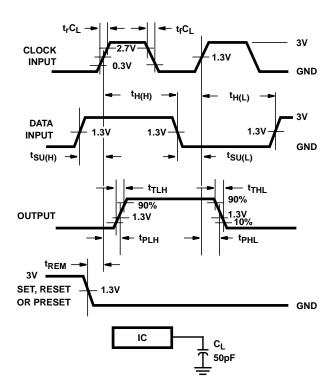


FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

Test Circuits and Waveforms (Continued) 6ns V_{CC} OUTPUT OUTPUT 90% DISABLE 50% DISABLE 10% 0.3 GND t_{PZL} → - t_{PLZ} → t_{PZL} ► t_{PLZ} → **OUTPUT LOW** OUTPUT LOW 50% TO OFF TO OFF 1.3V 10% 10% ◆ t_{PHZ} ◆ - t_{PZH} · t_{PHZ} → tpzh -90% 90% **OUTPUT HIGH OUTPUT HIGH** 50% TO OFF TO OFF 1.3V

OUTPUTS

ENABLED

FIGURE 7. HC THREE-STATE PROPAGATION DELAY WAVEFORM

OUTPUTS

DISABLED

OUTPUTS

ENABLED

FIGURE 8. HCT THREE-STATE PROPAGATION DELAY WAVEFORM

OUTPUTS

DISABLED

OUTPUTS

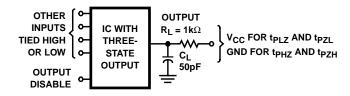
ENABLED

3V

GND

OUTPUTS

ENABLED



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC} , $C_L = 50pF$.

FIGURE 9. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8780601RA	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8780601RA CD54HC299F3A	Samples
5962-8943601MRA	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8943601MR A CD54HCT299F3A	Samples
CD54HC299F	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC299F	Samples
CD54HC299F3A	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8780601RA CD54HC299F3A	Samples
CD54HCT299F3A	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8943601MR A CD54HCT299F3A	Samples
CD74HC299E	ACTIVE	PDIP	N	20	20	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC299E	Samples
CD74HC299M	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC299M	Samples
CD74HC299M96	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC299M	Samples
CD74HC299M96E4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC299M	Samples
CD74HCT299E	ACTIVE	PDIP	N	20	20	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT299E	Samples
CD74HCT299M	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT299M	Samples
CD74HCT299M96	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT299M	Samples
CD74HCT299M96G4	ACTIVE	SOIC	DW	20	2000	TBD	Call TI	Call TI	-55 to 125		Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

PACKAGE OPTION ADDENDUM

www.ti.com 13-Jul-2022

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF CD54HC299, CD54HCT299, CD74HC299, CD74HCT299:

Catalog: CD74HC299, CD74HCT299

Military: CD54HC299, CD54HCT299

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Jan-2022

TAPE AND REEL INFORMATION





		Dimension designed to accommodate the component width
E	30	Dimension designed to accommodate the component length
K	(0	Dimension designed to accommodate the component thickness
	N	Overall width of the carrier tape
F	21	Pitch between successive cavity centers

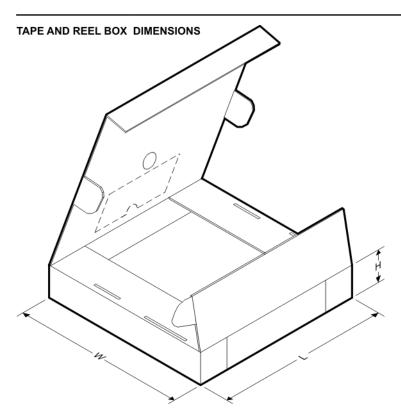
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC299M96	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
CD74HCT299M96	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

www.ti.com 5-Jan-2022



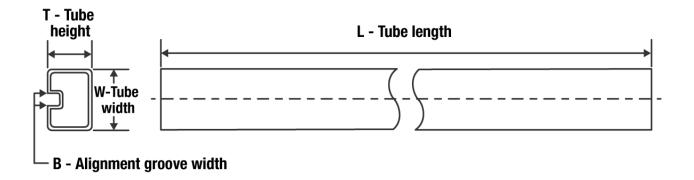
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CD74HC299M96	SOIC	DW	20	2000	367.0	367.0	45.0	
CD74HCT299M96	SOIC	DW	20	2000	367.0	367.0	45.0	

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Jan-2022

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD74HC299E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HC299M	DW	SOIC	20	25	507	12.83	5080	6.6
CD74HCT299E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HCT299M	DW	SOIC	20	25	507	12.83	5080	6.6

14 LEADS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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